

Nature of insulating state in NaV_2O_5 above charge-ordering transition: a cluster DMFT study

V. V. Mazurenko^{1,2}, A. I. Lichtenstein¹, M. I. Katsnelson^{1,2}, I. Dasgupta³, T. Saha-Dasgupta⁴ and V. I. Anisimov²

¹University of Nijmegen, NL-6525 ED Nijmegen, The Netherlands

²Institute of Metal Physics, Ekaterinburg, Russia

³Department of Physics, Indian Institute of Technology, Bombay, Mumbai 400 076;

⁴S.N. Bose National Center for Basic Sciences, JD Block, Salt Lake City, Calcutta 700 091

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The nature of insulating state driven by electronic correlations in the quarter-filled ladder compound $\alpha'\text{NaV}_2\text{O}_5$ is investigated within a cluster dynamical mean-field approach. An extended Hubbard model with first-principle tight-binding parameters have been used. It is shown that the insulating state in the charge-disordered phase of this compound is formed due to the transfer of spectral density and dynamical charge fluctuations where for the latter, the role of inter-site Coulomb interaction is found to be of crucial importance.

The ladder compound NaV_2O_5 has been a subject of great interest since last five years [1–10]. It exhibits a remarkable phase transition at $T_c = 34$ K, now identified as charge-ordering of *zigzag* type [2,4–7]. Both charge-ordered phase and charge-disordered one are insulating with an energy gap of the order of 0.8-1 eV [3]. The presence of the gap in the ordered phase is not surprising and it was reproduced successfully, for example, in the recent local density approximation(LDA)+U calculations [9]. The properties of the disordered phase are much more difficult to understand. In contrast to the iso-structural ladder compound, CaV_2O_5 , NaV_2O_5 has quarter-filled band [2] rather than half-filled one and cannot be considered as a *standard* Mott insulator [11]. It has been proposed in Ref. [5] that a large value of the transverse hopping parameter in the ladder which splits the band into sub-bands of the bonding and anti-bonding states [2] could be responsible for the Mott insulator behaviour in NaV_2O_5 in the presence of strong Coulomb interactions. However it is not known whether this mechanism is adequate for the realistic values of the parameters characterising the single-particle electronic structure and the electron-electron correlations.

In this letter we investigate the correlation effects in NaV_2O_5 taking into account non-local dynamical charge fluctuations on the rung for this two-leg ladder compound. This allows us to understand the origin of the insulating states above T_c and to estimate the relative importance of various physical mechanisms responsible for the gap formation.

The crystal structure of NaV_2O_5 projected in the xy plane is schematically shown in Fig.1. The results of the X-ray [6], NMR [7], and optical [3] experiments as well as the Hartree-Fock calculations [4] support the *zigzag* charge-ordering state for low temperatures (see Fig.1). In this state one has approximately one *d* electron per rung of the vanadium ladder. We start with LDA+U [12]

calculations of the ordered states but in contrast to the previous work [9] we considered several different types of the charge ordering. This gives us an opportunity to estimate the on-site and inter-site Coulomb interactions U and V respectively which in turn were used to parametrise the model Hamiltonians to be used for the calculations taking into account the dynamical correlation effects.

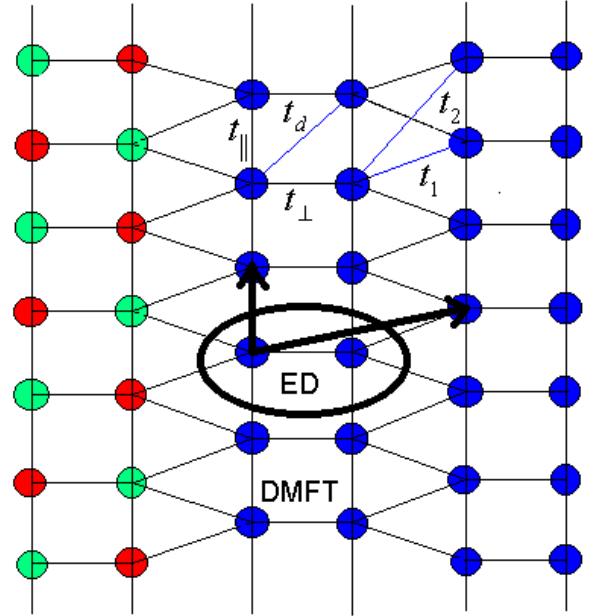


FIG. 1. Schematic representation of the crystal structure of the vanadium layers in NaV_2O_5 and the hopping matrix elements. The vanadium ions are denoted by filled circles. The ellipse shows the cluster which plays the role of an effective impurity in the DMFT calculations. A *zig-zag* charge ordering of the V^{4+} and V^{5+} ions, obtained from our LDA+U calculations as a ground state is shown on the left ladder. Bold arrows are the translation vectors.

By mapping the results of the LDA+U calculations for different types of charge ordering on the results of model calculations with on-site (U) and inter-site (V) Coulomb interaction parameters, we obtained the following values: $U=2.8$ eV and $V=0.17$ eV.

It is natural to assume that the tendency to keep the number of d electrons per rung close to unity also takes place above the transition temperature leading to strong short-range order and well-developed dynamical charge fluctuations. This is confirmed by the temperature dependences of the spin gap and the entropy measurements [10]. Usual LDA as well as the mean-field theories like Hartree-Fock or LDA+U methods are insufficient to take into account these essential many-body processes. The simplest reliable way to consider such short-ranged correlation effects is the use of the dynamical mean-field theory (DMFT) [13] which can be combined with realistic LDA band structure calculations (LDA+DMFT) [14–16]. The DMFT maps the initial many-body problem for a crystal onto a self-consistent quantum-impurity problem. To consider the phenomena such as charge ordering or fluctuations, the inter-site correlations are of crucial importance, therefore we need to use a cluster generalisation of the DMFT method [17–19]. The most reasonable choice of the cluster in our case is a pair of vanadium atom at the rung (see Fig.1). The unique geometry of the ladder compounds makes the choice of proper cluster simpler and the free cluster consideration is the most natural choice [18,19].

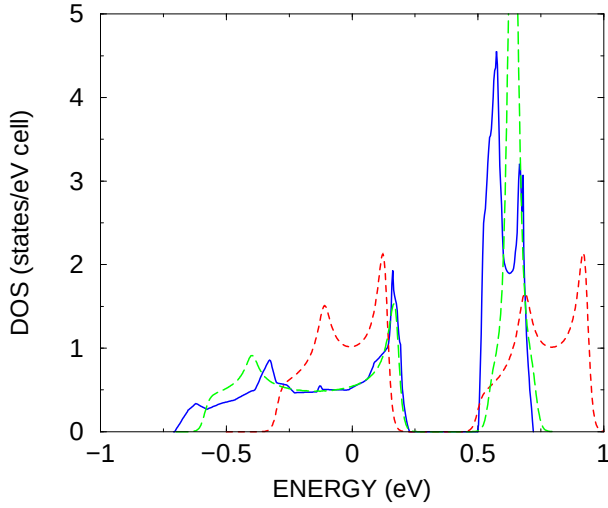


FIG. 2. Bare densities of states (DOS). Solid lines correspond to LDA DOS. The dashed and long dashed lines represent the first-principle tight-binding parameterisations without and with t_d hopping respectively.

We use the extended Hubbard model for two-leg ladder:

$$H = \sum_{ij} t_{ij} c_{i\sigma}^\dagger c_{j\sigma} + \sum_i U_i n_{i\uparrow} n_{i\downarrow} + \sum_{i<j,\sigma} V_{ij} n_{i\sigma} n_{j\sigma}$$

where t_{ij} -s are the effective hoppings, U_i and V_{ij} are local and inter-site Coulomb interactions respectively, $n_{i\sigma} = c_{i\sigma}^\dagger c_{i\sigma}$. The proper choice of hopping parameters is not simple, and the most widely used set ($t_\perp = 0.38$ eV, $t_\parallel = 0.18$ eV, $t_1 = 0.012$ eV, $t_2 = 0.03$ eV) was obtained by the fitting to the LDA bands [2]. Recently a rigorous procedure of *massive downfolding* of LDA bands to a few-band description and the subsequent Fourier transformation of the resulting Hamiltonian from the reciprocal to direct space to extract the single-electron parameters has been developed within the framework of linear-muffin-tin-orbital (LMTO) description [20]. This method applied to NaV_2O_5 gave the following set of hopping parameters: $t_\perp=0.398$ eV, $t_\parallel=0.084$ eV, $t_1=0.025$ eV, $t_2=0.022$ eV which is rather close to the standard one presented above, but in addition the *diagonal* (Fig. 1) hopping parameter $t_d=0.083$ eV is appreciable and was not considered before. We have found that these diagonal hopping processes are very important. As can be seen in Fig. 2, the inclusion of diagonal hopping t_d in the single-electron part of the model Hamiltonian provides a much better agreement of the bare DOS with the LDA DOS. It also results in the insulating state of the charge-disordered systems for the realistic values of U and V obtained from LDA+U calculations, while the other TB parametrisation, excluding the diagonal hopping, results into the metallic state for the same values of U and V (see Fig. 3).

The crystal Green function matrix in LDA+DMFT approach can be written as

$$\mathbf{G}(\mathbf{k}, i\omega) = [(i\omega + \mu) * \mathbf{1} - \mathbf{h}(\mathbf{k}) - \mathbf{\Sigma}(i\omega)]^{-1}$$

where $h_{\alpha\beta}(\mathbf{k})$ is the effective hopping matrix, $\Sigma_{\alpha\beta}(i\omega)$ is the self-energy matrix of the two-site super-cell dimension which is assumed to be local, i.e. $\mathbf{k}$ -independent, and μ is the chemical potential.

In the cluster version of the DMFT scheme [13,18], one can write the matrix equation for a bath Green function matrix $\mathcal{G}$ which describe an effective interactions with the rest of the crystal:

$$\mathcal{G}^{-1}(i\omega) = \mathbf{G}^{-1}(i\omega) + \mathbf{\Sigma}(i\omega) \quad (1)$$

where the local cluster Green function matrix is equal to $G_{\alpha\beta}(i\omega) = \sum_{\mathbf{k}} G_{\alpha\beta}(\mathbf{k}, i\omega)$, and the summation runs over the Brillouin zone of the lattice.

We used the exact diagonalisation (ED) scheme to solve the cluster DMFT problem. In this case the lattice Hamiltonian is mapped onto finite cluster impurity model:

$$H_{imp} = \sum_{i,j,\sigma} T_{ij} c_{i\sigma}^\dagger c_{j\sigma} + \sum_i U_i n_{i\uparrow} n_{i\downarrow} + \sum_{i<j,\sigma} V_{ij} n_{i\sigma} n_{j\sigma} \quad (2) \\ + \sum_{k,i,j,\sigma} E_{ij\sigma}(k) a_{ki\sigma}^\dagger a_{kj\sigma} + \sum_{k,i,j,\sigma} \Gamma_{ij\sigma}(k) (a_{ki\sigma}^\dagger c_{j\sigma} + h.c.)$$

where T_{ij} is the hopping parameters inside the cluster (for our two site rung-cluster this is only $t_{\perp}$), $E_{ij\sigma}(k)$, and $\Gamma_{ij\sigma}(k)$ are effective energies and hybridisation matrix for finite-chain bath orbitals $k = 1, \dots, n_b$.

For the iterative solution of the effective impurity model Eq.(2) we use the Lanczos version of ED method [13]. The orbital energy matrix for the conduction band $E_{ij\sigma}(k)$, and the corresponding hybridisation elements $\Gamma_{ij\sigma}(k)$, are the effective parameters which reproduce the bath Green function:

$$\mathcal{G}^{-1}(i\omega_n) = (i\omega_n + \mu) * \mathbf{1} - \mathbf{T} - \sum_k \mathbf{\Gamma}_k [i\omega_n - \mathbf{E}_k]^{-1} \mathbf{\Gamma}_k^+ \quad (3)$$

In the paramagnetic case we can transform $\mathcal{G}$, $\mathbf{T}$, $\mathbf{\Gamma}_k$, and $\mathbf{E}_k$ matrices of the dimension 2×2 for our cluster to the diagonal *bonding-antibonding* basis $\lambda = \{b, a\}$. In this case $T_{\lambda} = \{-t_{\perp}, t_{\perp}\}$ and $\mathcal{G}_{\lambda} = \{\mathcal{G}_b, \mathcal{G}_a\}$, where $\mathcal{G}_{b,a} = (\mathcal{G}_{11} \pm \mathcal{G}_{12})/2$. We used 10 bath orbitals for our two-site cluster.

The parameters $\{E_{k\lambda\sigma}, \Gamma_{k\lambda\sigma}\}$ are now fitted to reproduce the bath Green function $\mathcal{G}_{\lambda\sigma}(i\omega_{\nu})$ for bonding and anti-bonding states independently. The next step is the solution of the cluster-impurity problem (Eq. (2)) to get the cluster self-energies $\Sigma_{ij\sigma}(i\omega_{\nu})$ which are required for the next DMFT-iterations. After solving the effective cluster problem using Lanczos algorithm, the local Green's function matrix $G_{ij\sigma}(i\omega_{\nu})$ was determined and the cluster self-energy $\Sigma_{ij\sigma}(i\omega_{\nu})$ was obtained within the cluster-impurity scheme (Eq. (1)).

The phase diagram obtained in our DMFT calculations is shown in Fig. 3. One can see that for large enough U and realistic values of V the disordered state turns out to be insulating. This arises from the two physically different mechanisms. The first one is the spectral density transfer which can effectively change the quarter-filled system into the half-filled one. For large enough U the energy band splits into Hubbard sub-bands with the average spectral weight 1/2 for each of them and therefore the system appears to be insulator for half-filling instead of complete filling [21]. In this *large-U* limit the Hubbard model reduces to so-called t-J-V model and can explain insulating properties and optical spectra of NaV_2O_5 [22]. Our calculations do show a formation of the lower and upper Hubbard bands which leads to the spectral density transfer and moves the Fermi energy into the pseudo-gap between bonding and anti-bonding states in the lower Hubbard band as it was proposed qualitatively in Ref. [5]. However, the gap which can be obtained due to this mechanism is very small. To increase its value (consistent with the experiment [3]) the inclusion of the inter-site Coulomb repulsion (V) appears to be important (Fig. 4). Our calculations show that the broad enough gap arises with the increase of V suddenly, as a result of a first-order phase transition. With $V=0$ the insulator is

stable only for $U \approx 4$ eV and above, while already small value of $V=0.1$ eV decreases the critical U value below 3 eV. The results of LDA+U calculations ($U=2.8$ eV and $V=0.17$ eV) gave a point in the phase diagram (the cross on Fig. 3) which is well above the metal-insulator transition line. It is important to stress that if one carries out the calculation in usual single-site DMFT calculation instead of the cluster DMFT an adequate description of the electronic structure is not obtained for the same values of the parameters, and the insulating states appears only for $U > 12$ eV! This demonstrates the crucial importance of the charge fluctuations on the rung for the formation of insulating state in NaV_2O_5 with the realistic U -values. We also analysed the structure of the ground state in the effective cluster model (Eq.(2)) and found that for our LDA+U Coulomb parameters about 70% of the ground state eigenfunction corresponds to the configurations with one electron per rung and 20% related to empty rung states. This means that the configurations with the empty rungs in NaV_2O_5 has also appreciable weight.

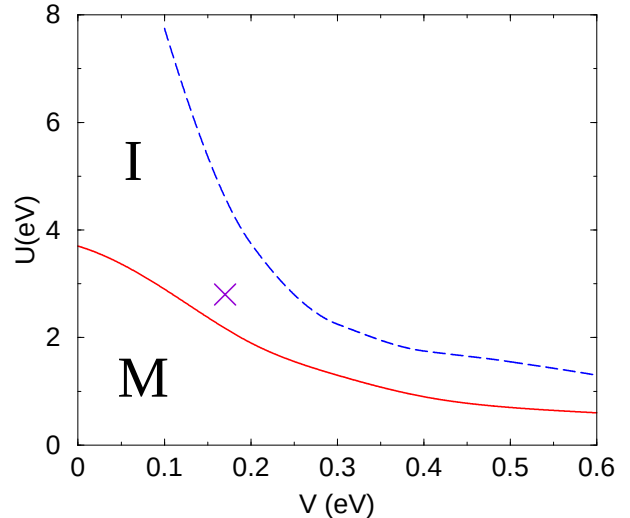


FIG. 3. Calculated phase diagram for the model with hopping parameter from Ref. [2] (dashed line) and the parameters obtained from our TB-LMTO calculation (solid line). The lines demarc the metallic and insulating phases in two calculations. The cross corresponds the values of U and V obtained from our LDA+U calculation.

We conclude that the insulating state of NaV_2O_5 above $T = 34$ K is characterised by strong dynamical charge fluctuations. In this respect the situation is close to the half-filled Hubbard chain or an *pseudospin-liquid* like phase: the tendency for the formation of the state with one electron per rung is similar to the singlet state formation in strongly frustrated spin systems and can be described in the limit of large U and V by anisotropic Heisenberg-like model [23,5,8,24]. It is important to

stress that experimentally the spin gap exists also above T_c [10]. However, this description is only qualitative.

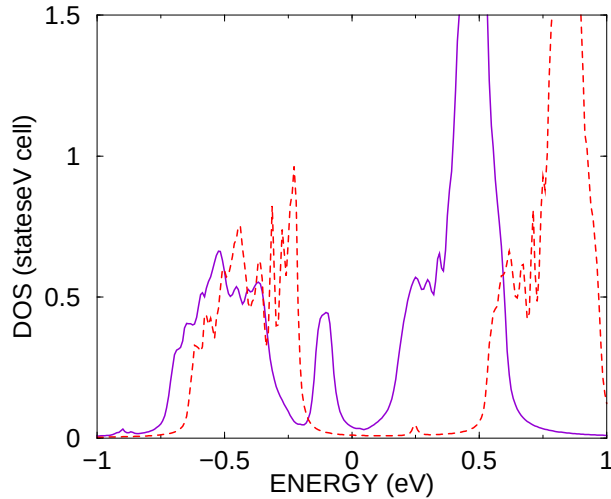


FIG. 4. The renormalised densities of state (only the lower Hubbard bands) obtained in our DMFT calculation with parameter $U=2.8$ eV and $V=0.17$ eV (solid line); $U=2.8$ eV and $V=0.5$ eV (dashed line).

Our calculations demonstrate that this compound is situated near the boundary between metal and insulator states and should be described by itinerant-electron models rather than by localised-electron ones. Since the metal-insulator transition in the model under consideration turns out to be strongly first-order type, the gap is not small. The value of the gap depends strongly on the inter-site Coulomb repulsion parameter V , as is demonstrated in Fig. 4. The insulating properties cannot be described correctly neglecting the charge fluctuations on the rung (too small values of V or using single-site DMFT approach instead of the cluster one).

To conclude, we present for the first time results on the cluster DMFT calculations for the insulating phase of NaV_2O_5 above charge-ordering transition using the extended Hubbard model with the first-principle tight-binding parameters. The non-local charge fluctuations and inter-site Coulomb interaction is of crucial importance for the formation of insulating state.

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